

L Number	Hits	Search Text	DB	Time stamp
1	55535	semiconductor and dram	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/04 14:41
2	13905	(semiconductor and dram) and (trench\$2 or recess\$2 or groove)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/04 14:42
3	979	((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/04 14:42
4	224	((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner) and collar and oxide	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/04 14:42
5	171	((((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner) and collar and oxide) and gate	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/04 14:43